Product data sheet

1. General description

Dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

2. Features and benefits

- Very low on-state loss
- Fast switching
- Low leakage current
- Low thermal resistance

3. Applications

- Active PFC in air conditioner
- Interleaved PFC topology in switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 127 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	15	А
Static chara	cteristics					
V _F	forward voltage	I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.1	1.8	V
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	25	50	ns





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1 A2
2	K	cathode		<u> </u>
3	A2	anode 2		K sym125
mb	mb	mounting base; connected to cathode		
			TO-247 (SOT429)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV415W-600P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_{R}	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 127 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	15	Α
I _{O(AV)}	average output current	$\bar{\delta}$ = 0.5; T _{mb} ≤ 127 °C; square-wave pulse; both diodes conducting	-	30	А
I _{FRM}	repetitive peak forward current	$δ$ = 0.5; t_p = 25 μs; T_{mb} ≤ 127 °C; Square-ware pulse	-	15	Α
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	165	Α
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

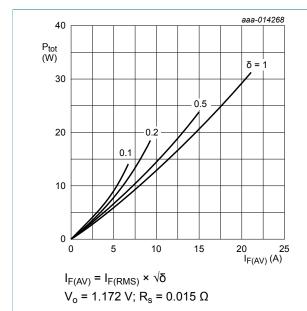


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

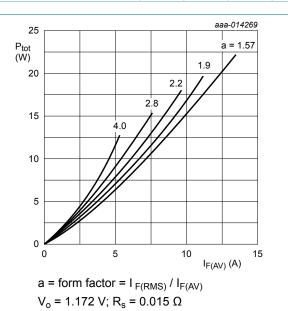


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

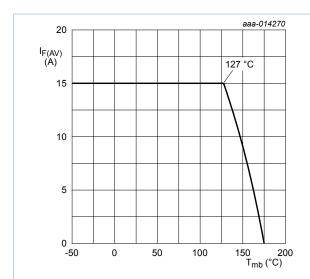


Fig. 3. Forward current as a function of mounting base temperature; maximum values

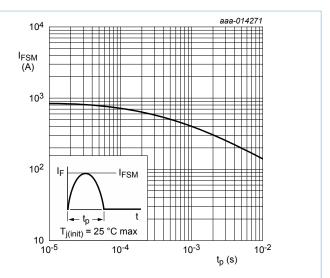


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; per diode; Fig. 5	-	1.2	2	K/W
		with heatsink compound; both diodes conducting	-	0.65	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	45	-	K/W

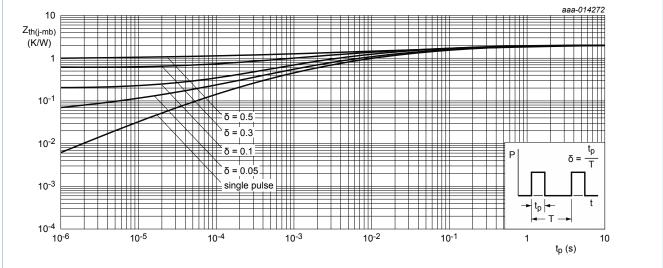


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

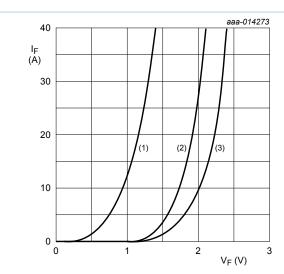
Table 6. Characteristics

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.4	2.1	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.1	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μΑ
		V _R = 600 V; T _j = 150 °C	-	-	500	μA
Dynamic cl	naracteristics		'			
Q _r	recovered charge	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	125	-	nC
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ μ s; $T_j = 125 \text{ °C}; Fig. 7$	-	318	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	25	50	ns
		I_F = 15 A; V_R = 400 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; Fig. 7	-	45	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	65	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$	-	34	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	5.5	-	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	9.7	-	Α

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Dual ultrafast power diode



 V_{o} = 1.172 V; R_{s} = 0.015 Ω

(1) T_j = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

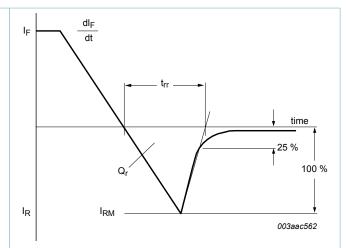
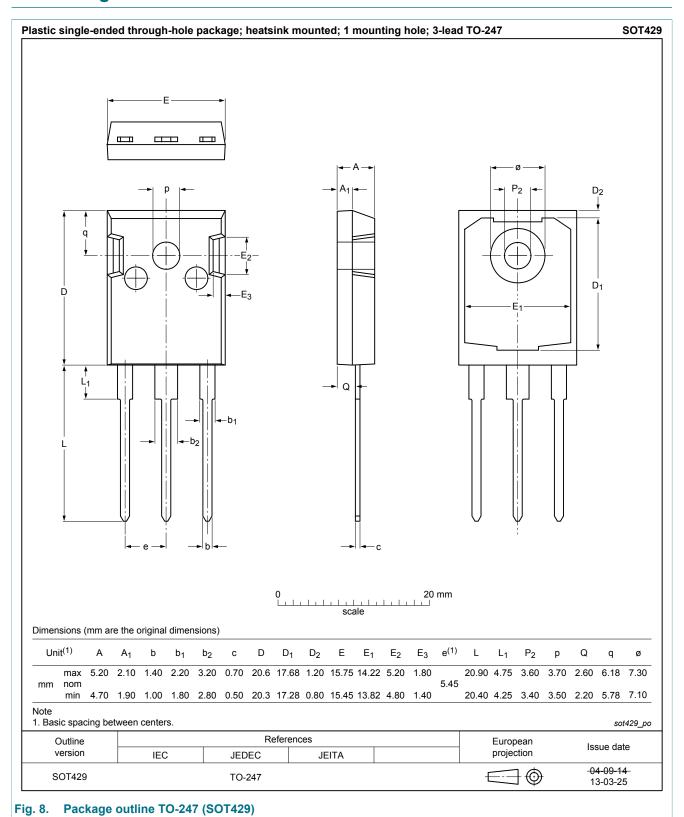


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline



11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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